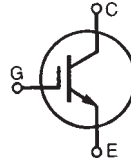
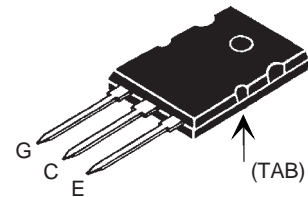
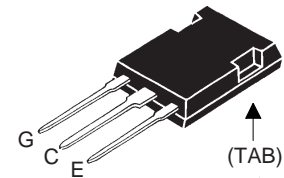


HiPerFAST™ IGBT
Lightspeed 2™ Series
IXGK 120N60C2
IXGX 120N60C2
 $V_{CES} = 600 \text{ V}$
 $I_{C110} = 120 \text{ A}$
 $V_{CE(sat)} = 2.5 \text{ V}$
 $t_{fi(typ)} = 45 \text{ ns}$


Symbol	Test Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^\circ\text{C to } 150^\circ\text{C}$	600	V
V_{CGR}	$T_J = 25^\circ\text{C to } 150^\circ\text{C}; R_{GE} = 1 \text{ M}\Omega$	600	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^\circ\text{C}$ (limited by leads)	75	A
I_{C110}	$T_C = 110^\circ\text{C}$ (die limit)	120	A
I_{CM}	$T_C = 25^\circ\text{C}, 1 \text{ ms}$	500	A
SSOA (RBSOA)	$V_{GE} = 15 \text{ V}, T_{VJ} = 125^\circ\text{C}, R_G = 4.7 \Omega$ Clamped inductive load @ $V_{CE} \leq 600 \text{ V}$	$I_{CM} = 200$	A
P_C	$T_C = 25^\circ\text{C}$	830	W
T_J		-55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
V_{ISOL}	50/60 Hz, RMS, $t = 1 \text{ minute}$ $I_{ISOL} < 1 \text{ mA}$ $t = 20 \text{ seconds}$	2500 3000	V~ V~
F_C	Clamping force	20..120/4.5..25	N/ib
T_L	Maximum lead temperature for soldering (Note 3)	300	$^\circ\text{C}$
T_{SOLD}	Plastic body for 10 seconds	260	$^\circ\text{C}$
Weight	TO-264 PLUS247	10 5	g g

TO-264(IXGK)

PLUS247(IXGX)


G = Gate C = Collector
E = Emitter Tab = Collector

Features

- Very high frequency IGBT
- Square RBSOA
- High current handling capability
- MOS Gate turn-on
- drive simplicity

Applications

- Uninterruptible power supplies (UPS)
- Switched-mode and resonant-mode power supplies
- AC motor speed control
- DC servo and robot drives
- DC choppers

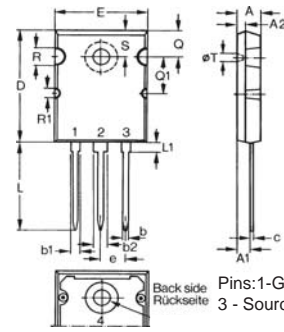
Advantages

- High power density
- Very fast switching speeds for high frequency applications
- High power surface mountable packages

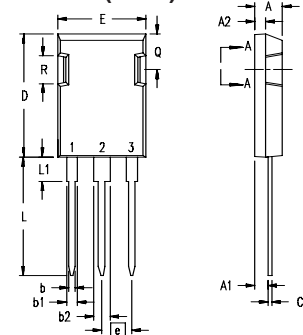
Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$ unless otherwise specified)		
		Min.	Typ.	Max.
BV_{CES}	$I_C = 1 \text{ mA}, V_{GE} = 0 \text{ V}$	600		V
$V_{GE(th)}$	$I_C = 500 \mu\text{A}, V_{CE} = V_{GE}$	3.0		V
I_{CES}	$V_{CE} = V_{CES}$ $V_{GE} = 0 \text{ V}$ $T_J = 125^\circ\text{C}$			100 μA 2 mA
I_{GES}	$V_{CE} = 0 \text{ V}, V_{GE} = \pm 20 \text{ V}$			$\pm 200 \text{ nA}$
$V_{CE(sat)}$	$I_C = I_T, V_{GE} = 15 \text{ V}$ Note 1 $T_J = 25^\circ\text{C}$ $T_J = 125^\circ\text{C}$		2.1 2.0	2.5 V V

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$ unless otherwise specified)		
		Min.	Typ.	Max.
g_{fs}	$I_C = 60\text{ A}; V_{CE} = 10\text{ V}$, Note 1	50	75	S
C_{ies}	$V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}, f = 1\text{ MHz}$		11	nF
C_{oes}			680	pF
C_{res}			190	pF
Q_g	$I_C = I_T, V_{GE} = 15\text{ V}, V_{CE} = 0.5 V_{CES}$		350	nC
Q_{ge}			72	nC
Q_{gc}			131	nC
$t_{d(on)}$	Inductive load, $T_J = 25^\circ\text{C}$ $I_C = 80\text{ A}, V_{GE} = 15\text{ V}$		18	ns
t_{ri}			25	ns
$t_{d(off)}$		$V_{CE} = 400\text{ V}, R_G = R_{off} = 1.0\ \Omega$		95
t_{fi}			45	ns
E_{off}		0.9	1.6	mJ
$t_{d(on)}$	Inductive load, $T_J = 125^\circ\text{C}$ $I_C = 80\text{ A}, V_{GE} = 15\text{ V}$		18	ns
t_{ri}			25	ns
E_{on}			1.6	mJ
$t_{d(off)}$	$V_{CE} = 400\text{ V}, R_G = R_{off} = 1.0\ \Omega$		130	ns
t_{fi}			85	ns
E_{off}		1.5	mJ	
R_{thJC}			0.15	K/W
R_{thJC}				K/W

Note: 1. Pulse test, $t \leq 300\ \mu\text{s}$, duty cycle $\leq 2\%$;
 2. Test current $I_T = 100\text{ A}$;
 3. Temperature measured at 1.6 mm (0.062 in.) from case for 10 seconds

TO-264 AA Outline


Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.82	5.13	.190	.202
A1	2.54	2.89	.100	.114
A2	2.00	2.10	.079	.083
b	1.12	1.42	.044	.056
b1	2.39	2.69	.094	.106
b2	2.90	3.09	.114	.122
c	0.53	0.83	.021	.033
D	25.91	26.16	1.020	1.030
E	19.81	19.96	.780	.786
e	5.46 BSC		.215 BSC	
J	0.00	0.25	.000	.010
K	0.00	0.25	.000	.010
L	20.32	20.83	.800	.820
L1	2.29	2.59	.090	.102
P	3.17	3.66	.125	.144
Q	6.07	6.27	.239	.247
Q1	8.38	8.69	.330	.342
R	3.81	4.32	.150	.170
R1	1.78	2.29	.070	.090
S	6.04	6.30	.238	.248
T	1.57	1.83	.062	.072

PLUS 247™ (IXGX) Outline


Terminals: 1 - Gate
 2 - Drain (Collector)
 3 - Source (Emitter)
 4 - Drain (Collector)

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.83	5.21	.190	.205
A ₁	2.29	2.54	.090	.100
A ₂	1.91	2.16	.075	.085
b	1.14	1.40	.045	.055
b ₁	1.91	2.13	.075	.084
b ₂	2.92	3.12	.115	.123
C	0.61	0.80	.024	.031
D	20.80	21.34	.819	.840
E	15.75	16.13	.620	.635
e	5.45 BSC		.215 BSC	
L	19.81	20.32	.780	.800
L1	3.81	4.32	.150	.170
Q	5.59	6.20	.220	0.244
R	4.32	4.83	.170	.190

IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585
4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405B2	6,759,692
4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6771478 B2